

# BYV32-200

## Switch-mode Power Rectifier

### Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 16 A Total (8 A Per Diode Leg)
- These Devices are Pb-Free and are RoHS Compliant\*

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

### Mechanical Characteristics

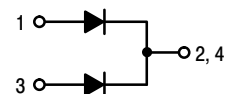
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:  
260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B  
Machine Model C



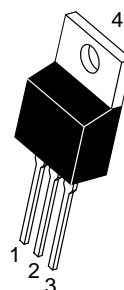
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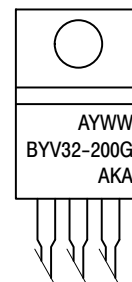
**ULTRAFAST RECTIFIER**  
**16 AMPERES, 200 VOLTS**  
 **$t_{rr} = 35 \text{ ns}$**



### MARKING DIAGRAM



**TO-220  
CASE 221  
STYLE 6**



A = Assembly Location  
Y = Year  
WW = Work Week  
BYV32-200 = Device Code  
G = Pb-Free Package  
AKA = Diode Polarity

### ORDERING INFORMATION

Device	Package	Shipping
BYV32-200G	TO-220 (Pb-Free)	50 Units / Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	200	V
Average Rectified Forward Current, $T_C = 156^\circ\text{C}$ Per Leg Total Device	$I_{F(AV)}$	8.0 16	A
Peak Rectified Forward Current (Square Wave, 20 kHz), $T_C = 154^\circ\text{C}$ – Per Diode Leg	$I_{FM}$	16	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	100	A
Operating Junction Temperature and Storage Temperature	$T_J, T_{stg}$	-65 to +175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**THERMAL CHARACTERISTICS**

Characteristic	Conditions	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{\theta JC}$	3.0	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	$R_{\theta JA}$	60	

**ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 1) ( $I_F = 5.0\text{ A}$ , $T_J = 100^\circ\text{C}$ ) ( $I_F = 20\text{ A}$ , $T_J = 25^\circ\text{C}$ )	$V_F$	– –	0.74 1.01	0.85 1.15	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 100^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ )	$I_R$	– –	21 3.5	600 50	$\mu\text{A}$
Maximum Reverse Recovery Time ( $I_F = 1.0\text{ A}$ , $di/dt = 50\text{ A}/\mu\text{s}$ ) ( $I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{REC} = 0.25\text{ A}$ )	$t_{rr}$	– –	– –	35 25	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 s, Duty Cycle  $\leq 2.0\%$

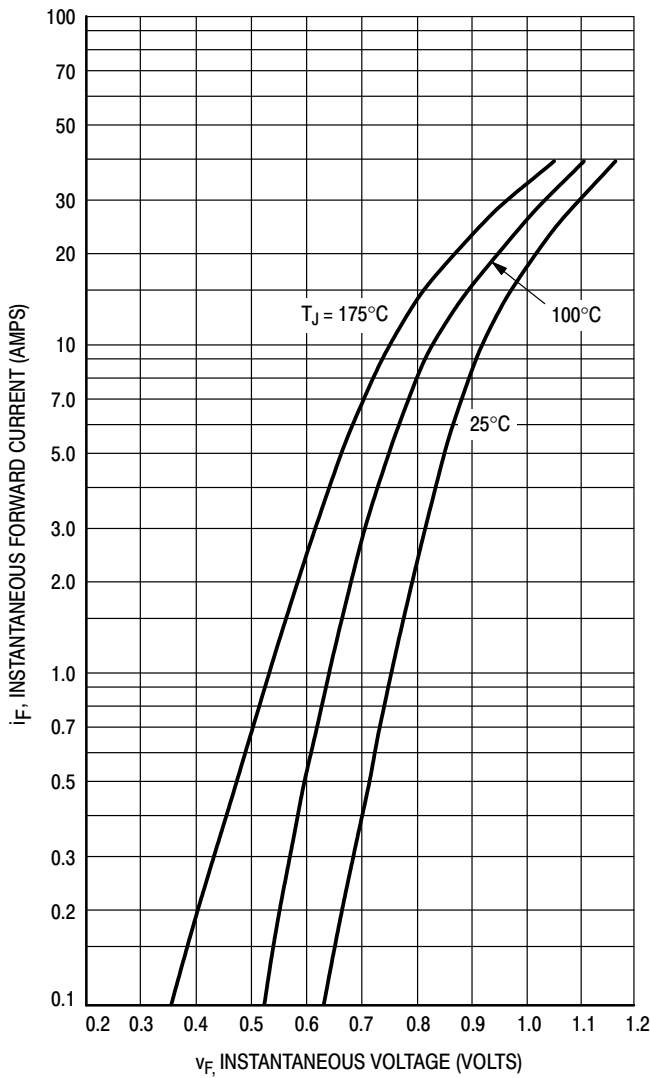


Figure 1. Typical Forward Voltage, Per Leg

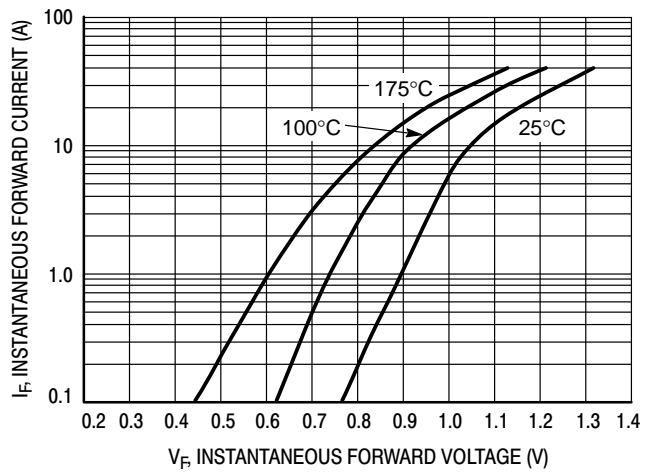


Figure 2. Maximum Forward Voltage

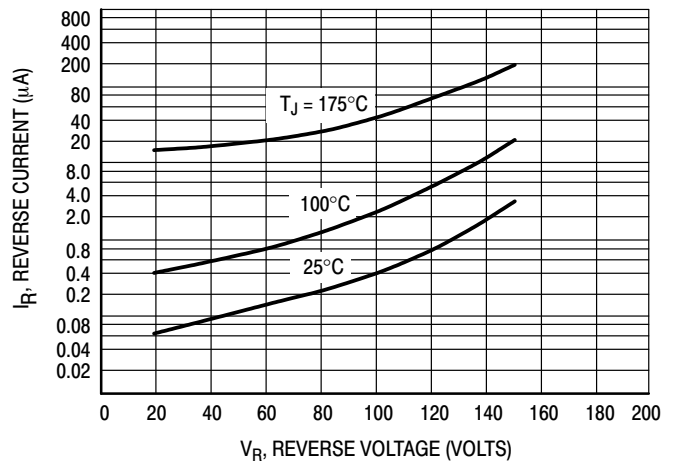


Figure 3. Typical Reverse Current, Per Leg\*

\* The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if  $V_R$  is sufficiently below rated  $V_R$ .

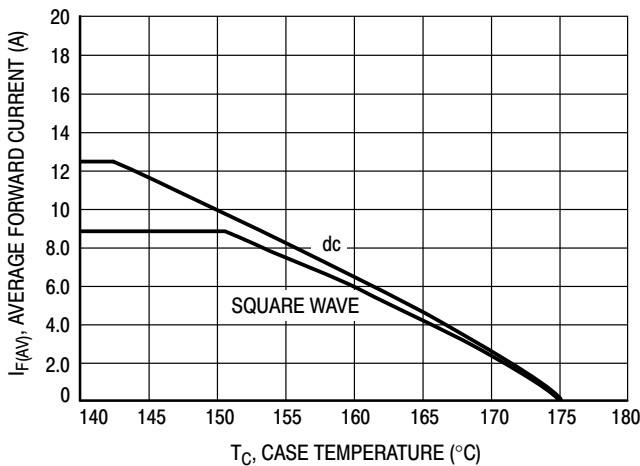


Figure 4. Current Derating, Case, Per Leg

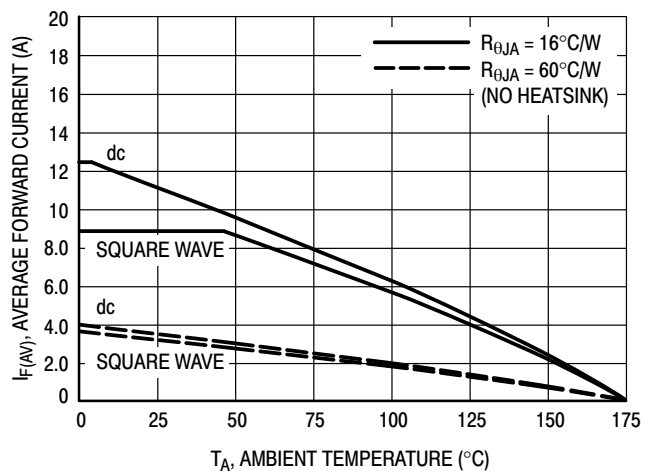


Figure 5. Current Derating, Ambient, Per Leg

# BYV32-200

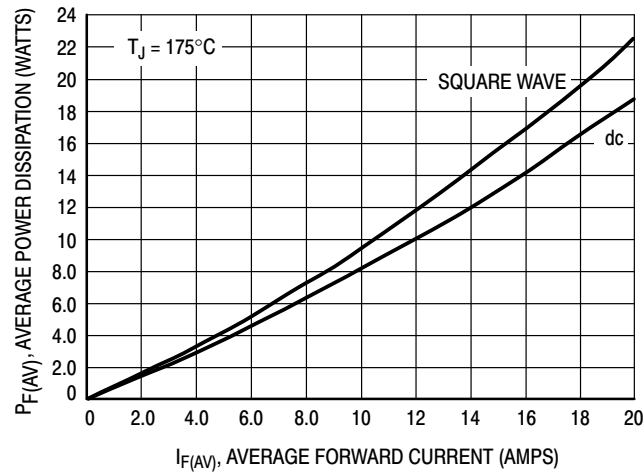


Figure 6. Power Dissipation, Per Leg

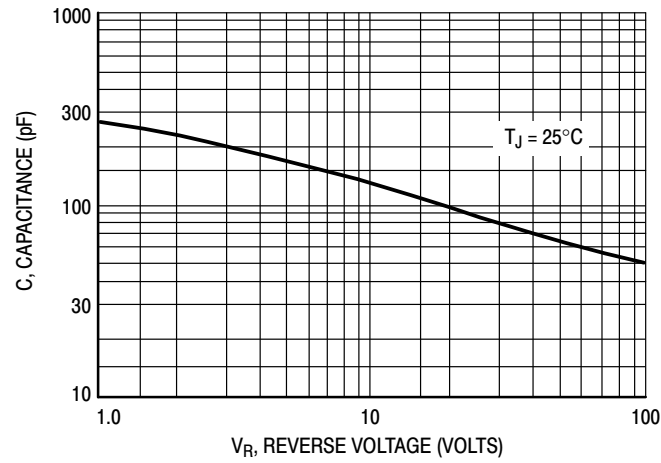


Figure 7. Typical Capacitance, Per Leg

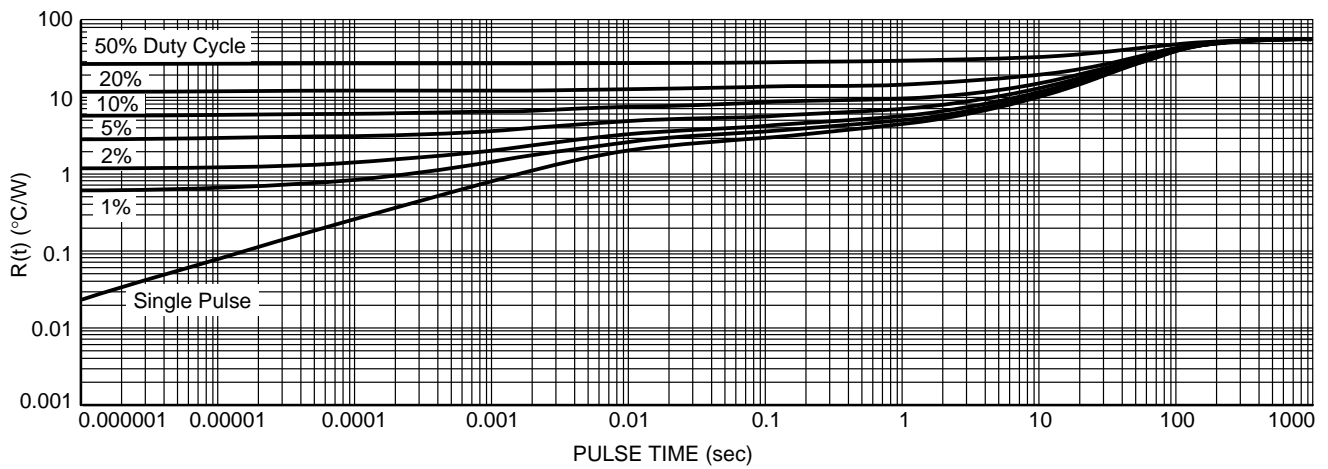
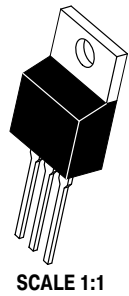


Figure 8. Thermal Response, Junction-to-Ambient

# MECHANICAL CASE OUTLINE

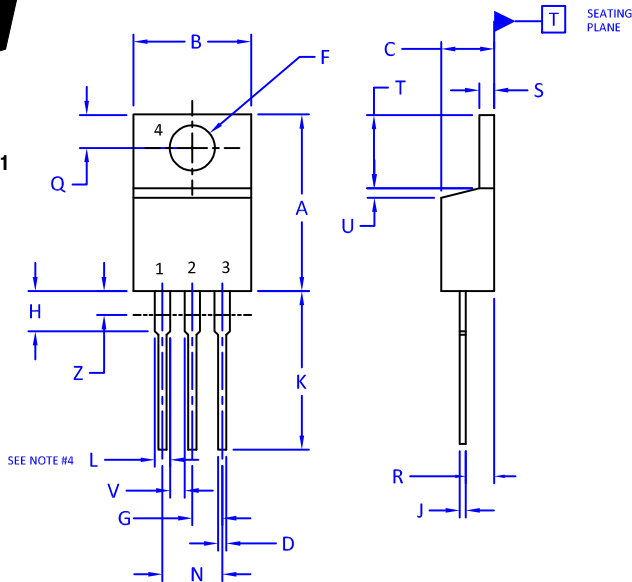
## PACKAGE DIMENSIONS

ON Semiconductor®



### TO-220 CASE 221A-09 ISSUE AJ

DATE 05 NOV 2019



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

#### STYLE 1:

- PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

#### STYLE 2:

- PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

#### STYLE 3:

- PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

#### STYLE 4:

- PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

#### STYLE 5:

- PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

#### STYLE 6:

- PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

#### STYLE 7:

- PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

#### STYLE 8:

- PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

#### STYLE 9:

- PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

#### STYLE 10:

- PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

#### STYLE 11:

- PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

#### STYLE 12:

- PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED


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DESCRIPTION: TO-220

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